

## DECLARATION AND POWER OF ATTORNEY

As a below named inventor, I hereby declare that:

My residence, post office address and citizenship are as stated below next to my name.

I believe I am the original, first and sole inventor (if only one name is listed below) or an original, first and joint inventor (if plural names are listed below) of the subject matter which is claimed and for which a patent is sought on the invention entitled: **A METHOD OF DEPOSITING TUNGSTEN NITRIDE USING A SOURCE GAS COMPRISING SILICON**; the specification of which is attached hereto.

I hereby state that I have reviewed and understand the contents of the above identified specification, including the claims.

I acknowledge the duty to disclose information which is material to patentability as defined in Title 37 of the Code of Federal Regulations, Section 1.56.

I hereby claim the benefit under Title 35 of the United States Code, Section 120 to which I am entitled and, insofar as the subject matter of each of the claims of this application is not disclosed in the prior United States application in the manner provided by the first paragraph of Title 35 of the United States Code, Section 112, I acknowledge the duty to disclose information which is material to patentability as defined in Title 37 of the Code of Federal Regulations, Section 1.56 which became available between the filing date of the prior application and the national or PCT international filing date of this application.

I hereby appoint the following attorney(s) and/or agent(s) to prosecute this application and to transact all business in the Patent and Trademark Office connected therewith:

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I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Title 18 of the United States Code, Section 1001 and that such willful false statements may jeopardize the validity of the application or any patent issued thereon.

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S/N 08/667,907IN THE UNITED STATES PATENT AND TRADEMARK OFFICEPATENT

Applicant: Scott G. Meikle et al.

Examiner: Thomas Bilodeau

Serial No.: 08/667,907

Group Art Unit: 1107

Filed: June 12, 1996

Docket: 303.444US2

Title: METHOD OF DEPOSITING TUNGSTEN NITRIDE USING A SOURCE GAS  
COMPRISING SILICONREVOCATION AND POWER OF ATTORNEY

Assistant Commissioner for Patents  
Washington, D.C. 20231

In accordance with 37 C.F.R. Section 1.36, M.P.E.P. Section 402.05, 402.07, and 324  
please revoke any existing Powers of Attorney, if any, and appoint the following attorneys and/or  
patent agents to prosecute this application and to transact all business in the Patent and  
Trademark Office in connection therewith:

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**CERTIFICATE UNDER 37 CFR §3.73(b)**

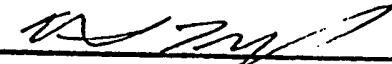
Micron Technology, Inc. hereby certifies that it is the assignee of the entire right, title and interest in the patent application identified above by virtue of an assignment from the inventor filed November 30, 1994 and recorded on Reel 7267, Frames 0790 - 0793. To the best of my knowledge and belief, title is in Micron Technology, Inc., the assignee.

Pursuant to 37 C.F.R. §3.73(b) I hereby declare that I, Michael L. Lynch, am empowered to sign this certificate on behalf of Micron Technology, Inc., the assignee.

I hereby declare that all statement made herein of my own knowledge are true, and that all statements made on information and belief are believed to be true.

Please direct all correspondence in this case to:

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Date November 1997 By   
Michael L. Lynch  
Title: Chief Patent Counsel  
Micron Technology, Inc.

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